

Notice of References Cited	Application/Control No. 10/619,922	Applicant(s)/Patent Under Reexamination JI ET AL.	
	Examiner Lynette T. Umez-Eronini	Art Unit 1765	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,797,639	09-2004	Carducci et al.	438/710
	B	US-6,403,491 B1	06-2002	Liu et al.	438/710
	C	US-6,242,359 B1	06-2001	Misra, Ashutosh	438/710
	D	US-5,176,790	01-1993	Arleo et al.	438/715
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Bigl et al., Reactive ion beam etching of silicon and silicon compounds - e.g. silicon dioxide or silicon nitride to give very high etching rate, December 3, 1980, English Abstract of DD 145348 A, 2 pages.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.